

# 960x960um Silicon PD Chip datasheet

P/N : WS9A-01C

## Application

Si PIN photodiode chip

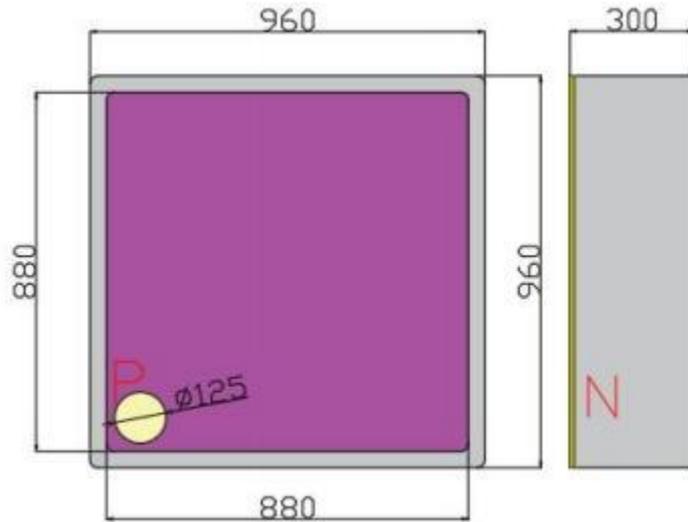
## Structure

Planar type : PIN diode

Electrodes :

Back side ( Cathode ) : Au

Top side (Anode) : Al



## DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	880±10 x 880±10			μm
Chip width	960			μm
Chip length	960			μm
Chip height	280	300	320	μm
Pad Area	125			μm

## Electro-Optical Characteristics ( @ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Sensitive Wavelength Range	λp		400	940	1100	nm
Reverse Dark Current	Id	Vr=10V			10	nA
Capacitance	Cj	VR=3V, f=1MHz		11		pF